

### **CONFIGURABLE MULTIPLE-FUNCTION GATE**

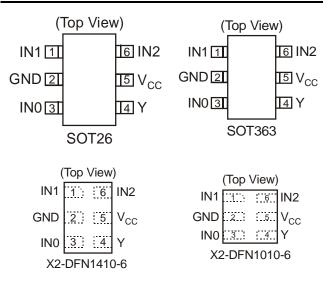
### Description

The 74LVC1G57 is a single 3-input positive configurable multiple function gate with a standard push-pull output. The output state is determined by eight patterns of 3-bit input. The user can chose the logic functions AND, OR, NAND, NOR, XNOR, inverter or noninverting buffer. All inputs can be connected to ground or Vcc as required. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down. The user is reminded that the device can simulate several types of logic gates but may respond differently due to the Schmitt action at the inputs.

#### Features

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22
  - 200-V Machine Model (A115-A)
  - 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- SOT26, SOT363, X2-DFN1410-6, and X2-DFN1010-6: Available in "Green" Molding Compound (no Br, Sb)
  - Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
  - Halogen and Antimony Free. "Green" Device (Note 3)

#### **Pin Assignments**



#### Applications

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide array of products such as:
  - PCs, networking, notebooks, netbooks, PDAs
  - Computer peripherals, hard drives, CD/DVD ROM
  - TV, DVD, DVR, set top box
  - Cell Phones, Personal Navigation / GPS
  - MP3 players ,Cameras, Video Recorders

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</li>

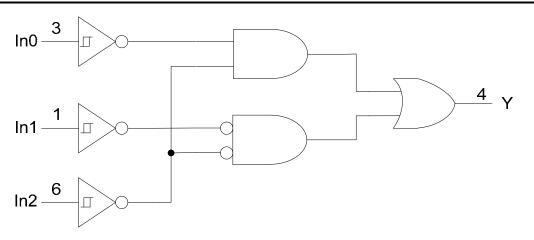


### **CONFIGURABLE MULTIPLE-FUNCTION GATE**

### **Pin Descriptions**

Pin Name	Function			
IN1	Data Input			
GND	Ground			
IN0	Data Input			
Y	Data Output			
V <sub>CC</sub>	Supply Voltage			
IN2	Data Input			

### Logic Diagram



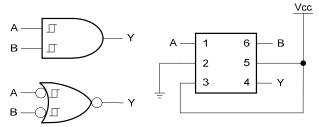
### **Function Table**

	Inputs	Output	
IN2	IN1	IN0	Y
L	L	L	Н
L	L	Н	L
L	н	L	Н
L	Н	Н	L
н	L	L	L
Н	L	Н	L
н	Н	L	Н
н	н	Н	Н

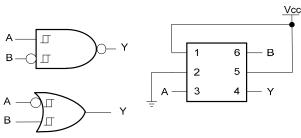


## CONFIGURABLE MULTIPLE-FUNCTION GATE

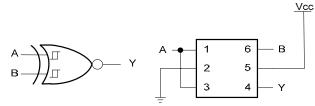
### Logic Configurations

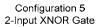


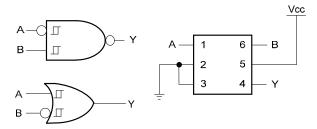
Configuration 1 2-Input AND Gate 2-Input NOR Gate with Both Inputs Inverted



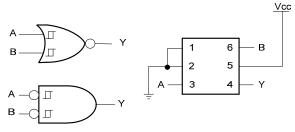
Configuration 3 2-Input NAND Gate with B Input Inverted 2-Input OR Gate with A Input Inverted



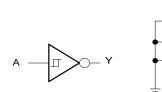


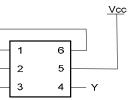


Configuration 2 2-Input NAND Gate with A Input Inverted 2-Input OR Gate with B input Inverted



Configuration 4 2-Input NOR Gate 2-Input AND Gate with Both Inputs Inverted





Configuration 6 Inverter

Function Selection Table						
Logic Function	Configuration					
2-input AND	1					
2-input AND with both inputs inverted	4					
2-input NAND with inverted input	2, 3					
2-input OR with inverted input	2, 3					
2-input NOR	4					
2-input NOR with both inputs inverted	1					
2-input XNOR	5					
1-input INVERTER	6					



## CONFIGURABLE MULTIPLE-FUNCTION GATE

### **Absolute Maximum Ratings (Note 4)**

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to +6.5	V
VI	Input Voltage Range	-0.5 to +6.5	V
Vo	Voltage applied to output in high impedance or IOFF state	-0.5 to +6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current VI<0	-50	mA
loк	Output Clamp Current	-50	mA
lo	Continuous output current	±50	mA
Continuous current through Vdd or GND		±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

Notes: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

### **Recommended Operating Conditions (Note 5)**

Symbol		Parameter	Min	Max	Unit		
		Operating	1.65	5.5	V		
V <sub>CC</sub>	Operating Voltage	Data retention only	1.5		V		
VI	Input Voltage		0	5.5	V		
Vo	Output Voltage		0	Vcc	V		
		V <sub>CC</sub> = 1.65V		-4			
		$V_{CC} = 2.3 V$		-8			
I <sub>OH</sub>	High-level output current			-16	mA		
		$V_{CC} = 3V$		-24			
		$V_{CC} = 4.5V$		-32			
		V <sub>CC</sub> = 1.65V		4			
		$V_{CC} = 2.3V$		8			
I <sub>OL</sub>	Low-level output current			16	mA		
		$V_{CC} = 3V$		24			
		$V_{CC} = 4.5V$		32			
		V <sub>CC</sub> = 1.8V ± 0.15V, 2.5V ± 0.2V		20			
Δt/ΔV	Input transition rise or fall rate	$V_{CC} = 3.3V \pm 0.3V$		10	ns/V		
		$V_{CC} = 5V \pm 0.5V$		5			
T <sub>A</sub>	Operating free-air temperature		-40	+125	٥C		

Notes: 5. Unused inputs should be held at V<sub>CC</sub> or Ground.



### **Electrical Characteristics** $T_A = -40^{\circ}C$ to $+85^{\circ}C$ (All typical values are at $V_{CC} = 3.3V$ , $T_A = +25^{\circ}C$ )

Symbol	Parameter	Test Conditions	V <sub>cc</sub>	Min	Тур.	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
V <sub>T+</sub>	Positive-going input		3V	1.50		2.00	
	threshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.72	
			2.3V	0.58		1.00	
V <sub>T-</sub>	Negative-going input		3V	0.80		1.30	
	threshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
			2.3V	0.40		0.80	
ΔVT			3V	0.35		1.00	
(V	(V <sub>T+</sub> - V <sub>T-)</sub>		4.5V	0.55		1.10	
			5.5V	0.60		1.20	
		I <sub>OH</sub> = -100µА	1.65V to 5.5V	Vcc -0.1			
		I <sub>OH</sub> = -4mA	1.65V	1.2			
N/	List Local Octoor Michael	I <sub>OH</sub> = -8mA	2.3V	1.9			
V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = -16mA	01/	2.4			V
		I <sub>OH</sub> = -24mA	3V	2.3			
		I <sub>OH</sub> = -32mA	4.5V	3.8			
		I <sub>OL</sub> = 100μA	1.65V to 5.5V			0.1	
		$I_{OL} = 4mA$	1.65V			0.45	
N/	LPak Isosel Isoset Malta as	I <sub>OL</sub> = 8mA	2.3V			0.3	
V <sub>OL</sub>	High-level Input Voltage	I <sub>OL</sub> = 16mA	01/			0.4	V
		$I_{OL} = 24 \text{mA}$	3V			0.55	
		I <sub>OL</sub> = 32mA	4.5V			0.55	
h	Input Current	$V_I = 5.5V$ or GND	0 to 5.5V			±5	μA
I <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 5.5V$	0			± 10	μA
Icc	Supply Current	V <sub>I</sub> = 5.5V of GND I <sub>O</sub> =0	1.65V to 5.5V			10	μA
ΔI <sub>CC</sub>	Additional Supply Current	One input at $V_{CC}$ -0.6V Other inputs at $V_{CC}$ or GND	3V to 5.5V			500	μA



### **Electrical Characteristics** $T_A = -40^{\circ}C$ to $+125^{\circ}C$ (All typical values are at $V_{CC} = 3.3V$ , $T_A = +25^{\circ}C$ )

Symbol	Parameter	Test Conditions	V <sub>cc</sub>	Min	Тур.	Max	Unit	
			1.65V	0.70		1.20		
	Positive-going input		2.3V	1.11		1.60		
$V_{T+}$	Positive-going input threshold voltage		3V	1.50		2.00		
	theshold voltage		4.5V	2.16		2.74		
			5.5V	2.61		3.33		
			1.65V	0.30		0.75		
			2.3V	0.58		1.03		
V <sub>T</sub> .	Negative-going input threshold voltage		3V	0.80		1.33		
	theshold voltage		4.5V	1.21		1.95		
			5.5V	1.45		2.35		
			1.65V	0.30		0.62		
			2.3V	0.37		0.80		
$\Delta V_{T}$	Hysteresis (V <sub>T+</sub> - V <sub>T-)</sub>		3V	0.32		1.00		
(VT+ - VT-)	(VT+- VT-)		4.5V	0.50		1.20		
			5.5V	0.55		1.40		
		I <sub>OH</sub> = -100μA	1.65V to 5.5V	V <sub>CC</sub> -0.1				
		I <sub>OH</sub> = -4mA	1.65V	0.95				
		I <sub>OH</sub> = -8mA	2.3V	1.7			N	
V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = -16mA	0)/	1.9			V	
		I <sub>OH</sub> = -24mA	3V	2.0				
		I <sub>OH</sub> = -32mA	4.5V	3.4				
		I <sub>OL</sub> = 100μA	1.65V to 5.5V			0.1		
		$I_{OL} = 4mA$	1.65 V			0.7		
N/		I <sub>OL</sub> = 8mA	2.3V			0.45	N	
V <sub>OL</sub>	High-level Input Voltage	I <sub>OL</sub> = 16mA	2)/			0.6	V	
		$I_{OL} = 24 \text{mA}$	3V			0.8		
		$I_{OL} = 32mA$	4.5V			0.8		
I	Input Current	$V_I = 5.5 V \text{ or GND}$	0 to 5.5V			± 100	μA	
I <sub>OFF</sub>	Power Down Leakage Current	$V_{I} \text{ or } V_{O} = 5.5 V$	0			± 200	μA	
Icc	Supply Current	V <sub>1</sub> = 5.5V of GND I <sub>O</sub> =0	1.65V to 5.5V			200	μA	
ΔI <sub>CC</sub>	Additional Supply Current	One input at $V_{CC}$ –0.6V Other inputs at $V_{CC}$ or GND	3V to 5.5V			5000	μA	



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### **Package Characteristics** (All typical values are at $V_{CC} = 3.3V$ , $T_A = +25^{\circ}C$ )

Symbol	Parameter	Test Conditions	V <sub>cc</sub>	Min	Тур.	Max	Unit		
Cı	Input Capacitance	$V_I = V_{CC} - or GND$	3.3		3.5		pF		
		SOT26			204				
	θ <sub>JA</sub> Thermal Resistance Junction- to-Ambient	SOT363			371		°C/W		
$\theta_{JA}$		X2-DFN1410-6	(Note 6)		430				
		X2-DFN1010-6			510		1		
		SOT26			52				
	Thermal Resistance Junction-	SOT363			143		0		
$\theta_{\rm JC}$	to-Case	X2-DFN1410-6	(Note 6)		190		°C/W		
		X2-DFN1010-6			250		1		

Notes: 6. Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

### **Switching Characteristics**

Parameter	From	TO		V <sub>CC</sub> = 1.8V ± 0.15V		V <sub>CC</sub> = 2.5V ± 0.2V		V <sub>CC</sub> = 3.3V ± 0.3V		V <sub>CC</sub> = 5V ± 0.5V	
	(Input)	(OUTPUT)	Min	Мах	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Y	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns

#### $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$ , $C_L = 30 \text{ or } 50\text{pF}$ as noted (see Figure 1)

Parameter	From	TO	V <sub>CC</sub> = 1.8V ± 0.15V				V <sub>CC</sub> = 3.3V ± 0.3V		V <sub>CC</sub> = 5V ± 0.5V		Unit
	(Input)	(OUTPUT)	Min	Мах	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Y	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

### **Operating Characteristics**

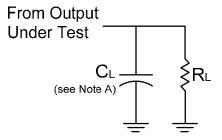
T <sub>A</sub> =	+25°C
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	Parameter	Test Conditions	Vcc = 1.8V Typ.	Vcc = 2.5V Typ.	Vcc = 3.3V Typ.	Vcc = 5V Typ.	Unit
C <sub>pd</sub>	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF

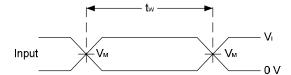


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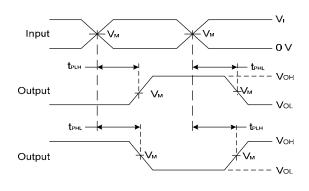
### **Parameter Measurement Information**



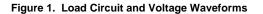
V	Inj	outs			Р
V <sub>CC</sub>	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	CL	RL
1.8V ±0.15V	V <sub>CC</sub>	≤ 2ns	V <sub>CC</sub> /2	30pF	1ΚΩ
2.5V ±0.2V	V <sub>CC</sub>	≤ 2ns	V <sub>CC</sub> /2	30pF	500Ω
3.3V ±0.3V	3V	≤ 2.5ns	1.5V	50pF	500Ω
5V ±0.5V	V <sub>CC</sub>	≤ 2.5ns	V <sub>CC</sub> /2	50pF	500Ω



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Notes:

- A. Includes test lead and test apparatus capacitance.
- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz
- C. Inputs are measured separately one transition per measurement
- D.  $t_{\text{PLH}}$  and  $t_{\text{PHL}}$  are the same as  $t_{\text{PD}}$



### **CONFIGURABLE MULTIPLE-FUNCTION GATE**

#### **Ordering Information** 74LVC1G 57 XXX - 7 Function Package Logic Device Packing 74 : Logic Prefix 57: 3-Input W6 : SOT26 7: Tape & Reel LVC: 1.65 to 5.5V DW : SOT363 Configurable Family FW4: X2-DFN1010-6 Multiple-Function FZ4 : X2-DFN1410-6 1G: One gate Gate 7" Tape and Reel Packaging Device Package Code

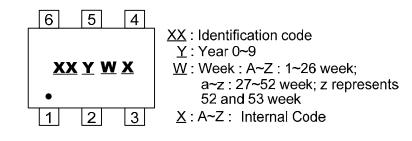
	Bernoe	T dokuge oode	(Note 7)	Quantity	Part Number Suffix
<b>Pb</b> ,	74LVC1G57W6-7	W6	SOT26	3000/Tape & Reel	-7
PD,	74LVC1G57DW-7	DW	SOT363	3000/Tape & Reel	-7
PD,	74LVC1G57FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
PD.	74LVC1G57FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7

Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



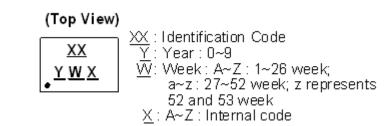
### **Marking Information**

#### (1) SOT26, SOT363



Part Number	Package	Identification Code
74LVC1G57W6	SOT26	TW
74LVC1G57DW	SOT363	TW

#### (2) X2-DFN1010-6, X2-DFN1410-6



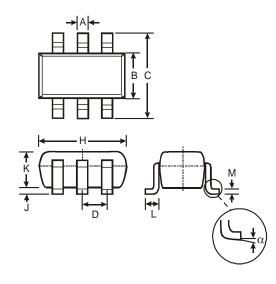
Part Number	Package	Identification Code
74LVC1G57FW4	X2-DFN1010-6	TW
74LVC1G57FZ4	X2-DFN1410-6	TW



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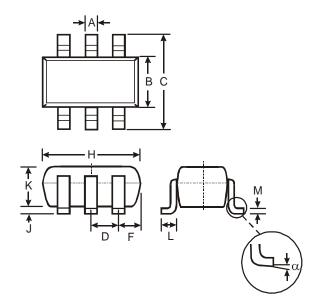
### Package Outline Dimensions (All Dimensions in mm)

### (1) SOT26



	SOT26			
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
в	1.50	1.70	1.60	
c	2.70	3.00	2.80	
D			0.95	
Н	2.90	3.10	3.00	
<b>ر</b>	0.013	0.10	0.05	
κ	1.00	1.30	1.10	
1	0.35	0.55	0.40	
М	0.10	0.20	0.15	
α	0°	8°		
All D	imensi	ons in	mm	

#### (2) SOT363



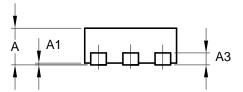
	SOT363			
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
C	2.00	2.20		
D	0.65	0.65 Typ		
F	0.40	0.45		
Н	1.80	2.20		
J	0	0.10		
К	0.90	1.00		
L	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Di	mensions	in mm		

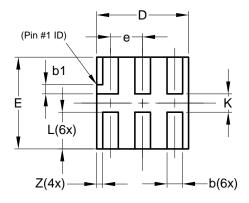


## CONFIGURABLE MULTIPLE-FUNCTION GATE

### Package Outline Dimensions (All Dimensions in mm)

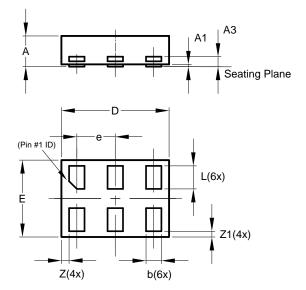
#### (3) X2-DFN1010-6





X2-DFN1010-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3	_	_	0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е	_		0.35	
L	0.35	0.45	0.40	
κ	0.15			
Ζ			0.065	
All	Dimens	sions in	mm	

#### (4) X2-DFN1410-6



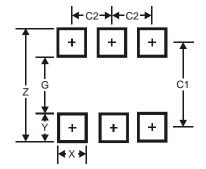
	X2-DFN1410-6			
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3	_	—	0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е			0.50	
L	0.25	0.35	0.30	
Z		_	0.10	
Z1	0.045	0.105	0.075	
All I	Dimensi	ions in I	mm	



## CONFIGURABLE MULTIPLE-FUNCTION GATE

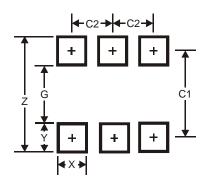
### **Suggest Pad Layout**

#### (1) SOT26



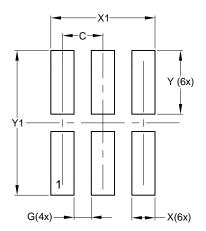
Dimensions	Value (in mm)
Z	3.20
G	1.60
х	0.55
Y	0.80
C1	2.40
C2	0.95

(2) SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

#### (3) X2-DFN1010-6



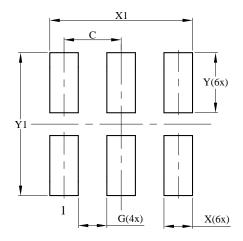
Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
¥1	1.250



## CONFIGURABLE MULTIPLE-FUNCTION GATE

### Suggest Pad Layout

#### (4) X2-DFN1410-6



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Y	0.525
Y1	1.250



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